

Appl. No. 10/707,932  
Amdt. dated November 23, 2005  
Reply to Office action of September 07, 2005

**Amendments to the Specification:**

Please substitute Paragraph [0019] with the following amended text:

The passivation structure 116 is made of an organic/inorganic film. By changing the ratio between the sources of the organic compounds and the inorganic compounds continuously in the fabricating process, the formed organic/inorganic film has a higher organic/inorganic ratio  $[[an]]$  in inner side 115, which is closer to the display unit 114, of the passivation structure 116 than that in an outer side 117, which is farther from the display unit 114, and the organic/inorganic ratio gradually decreases from the inner side 115 of the passivation structure 116 toward the outer side 117 of the passivation structure 116.

Please substitute Paragraph [0020] with the following amended text:

For example, in the preferred embodiment of the present invention, trimethylchlorosilane (TMCS) or hexamethyl disilazane (HMDS) is used as the gas source to perform a plasma enhanced chemical vapor deposition with an oxygen plasma and thereby produce an organic/inorganic film formed of a  $SiO_xC_yH_z$  compound covering the display unit 114 and the substrate 112. In the fabricating process, different methods can be used to control the ratio among x, y, and z so that the  $SiO_xC_yH_z$  compound formed earlier has a higher organic/inorganic ratio, which has a higher y and z, and the organic/inorganic ratio is decreasing gradually, in which y and z are smaller, in the latter fabrication. Therefore, the inner side 115 closer to the display unit 114 of the passivation structure 116 has a similar property to the organic materials so that a better attachment and a thermal expansion coefficient and stress, which are corresponding to the display unit 114, can be obtained. The outer side 117 of the passivation structure 116, which is

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farther from the display unit 114, has a lower organic/inorganic ratio and thereby has a high water repelling ability, which is similar to the inorganic materials. It is important that the passivation structure 116 is not only fabricated by the aforementioned PECVD process but also can be formed in  
5 other processes, such as a sputtering process. In addition, though the  $\text{SiO}_x\text{C}_y\text{H}_z$  compound is disclosed in the previous embodiment, however, the organic/inorganic film can also be composed of other materials, such as  $\text{SiN}_x\text{C}_y\text{H}_z$ , or  $\text{SiO}_w\text{N}_x\text{C}_y\text{H}_z$  compounds.